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METHOD AND APPARATUS FOR ETCHING SILICON

Abstract of the Disclosure

An etching method and an etching apparatus for applying an etchant 38 containing nitric acid and hydrofluoric acid to silicon 10 to etch the silicon. The etchant used in etching is recovered, and brought into contact with a gas 72 inert to the etchant, whereby the etchant is regenerated. At least a part of the regenerated etchant is reused in etching.

Figure 1



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